

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

General Description

The MAX5879 is a high-performance, 14-bit, 2.3Gsps digital-to-analog converter (DAC) capable of synthesizing high-frequency and wideband signals in baseband and higher-order Nyquist zones. The 2.3Gsps update rate, combined with the selectable frequency-response modes (NRZ, RZ, RF, and RFZ), allows digital generation of signals to more than 2GHz output frequency. The unique RFZ mode allows generation up to the 6th Nyquist zone, with update rates to 1150Msps. The device features excellent spurious, noise, and intermodulation distortion performance, and can directly synthesize signal bandwidths to more than 1GHz.

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The device has four 14-bit, multiplexed, low-voltage differential signaling (LVDS) input ports that each operates up to 1150Mwps. The DAC operates with a clock rate (f_{CLK}) up to 2.3GHz. The device has a selectable 2:1 or 4:1 input multiplexer that allows the user to select two data ports up to 1150Mwps each, or four data ports up to 575Mwps each. In turn, the input data rate is 1/2 or 1/4 the DAC update rate at each port. The device features a delay-locked loop (DLL) to ease data synchronization with FPGAs or ASICs. The parity input and parity error flag output can be used to detect bit errors between the data source and the DAC. The device also features a data clock reset circuit for aligning the data-capture clocks of multiple DACs.

The device has four selectable frequency-response output modes:

- Nonreturn-to-zero (NRZ) mode provides the highest dynamic range/output power in the 1st Nyquist zone.
- Return-to-zero (RZ) mode trades off SNR for improved gain flatness in the 1st, 2nd, and 3rd Nyquist zones.
- Radio-frequency (RF) mode provides higher SNR and excellent dynamic performance in the 2nd and 3rd Nyquist zones.
- Radio-frequency-return-to-zero (RFZ) mode provides high dynamic range and improved gain flatness in the 3rd through 6th Nyquist zones at a maximum update rate of f_{CLK}/2.

The device is a current-steering DAC with an integrated 50Ω differential output termination to ensure optimum dynamic performance. Operating from 3.3V and 1.8V power supplies, the device dissipates 1.8W at 40mA full-scale current and 2.3W at 80mA full-scale current. The device is specified over the -40°C to +85°C extended temperature range and is offered in a 256-ball (17mm x 17mm) CSBGA package.

Ordering Information appears at end of data sheet.

Features

- Industry-Leading Performance
 - ♦ WCDMA ACLR: 70dB at 2.14GHz
 - DOCSIS ACP: -70dBc at 400MHz, 8 Channel (256 QAM)
 - $\diamond\,$ Noise Density: -165dBc/Hz at 200MHz
- High Output Power: 9dBm (CW)
- Frequency-Response Modes: NRZ, RZ, RF, RFZ
- 2GHz Output Bandwidth
- 2:1 or 4:1 Multiplexed LVDS Inputs
 - ♦ Up to 1150MHz Each Port
 - ♦ Single or Double Data-Rate Operation
- On-Chip DLL for Input Data Synchronization
- Reset Function for Multiple DAC Synchronization

Applications

Broadband Communications Edge QAM and CMTS Digital Video Broadcast Wireless Infrastructure

Software-Defined Radio Direct Digital Synthesis Radar and Avionics Arbitrary Waveform Generators

Functional Diagram



For related parts and recommended products to use with this part, refer to <u>www.maximintegrated.com/MAX5879.related</u>.

For pricing, delivery, and ordering information, please contact Maxim Direct at 1-888-629-4642, or visit Maxim's website at www.maximintegrated.com.

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ABSOLUTE MAXIMUM RATINGS

AV _{DD3.3} to GND, DACREF0.3V to +3.6V	DDN0–DDN13, XORN, SYNCN,
V _{DD1.8} , AV _{CLK} to GND, DACREF0.3V to +2.0V	PARN to GND, DACREF0.3V to (V _{DD1.8} + 0.3V)
REFIO, FSADJ to GND, DACREF0.3V to (VAVDD3.3 + 0.3V)	DCLKP, DCLKN to GND, DACREF0.3V to (V _{DD1.8} + 0.3V)
OUTP, OUTN to GND, DACREF0.3V to (VAVDD3.3 + 1.0V)	DCLKRSTP, DCLKRSTN to GND,
CREF to GND, DACREF0.3V to +2.0V	DACREF0.3V to (V _{DD1.8} + 0.3V)
DCLKDIV, DLLOFF, DELAY,	SO/LOCK, PERR to GND, DACREF0.3V to (V _{DD1.8} + 0.3V)
REFRES to GND, DACREF0.3V to (V _{AVDD3.3} + 0.3V)	SO/LOCK, PERR Continuous Current
SE, MUX, RF, RZ to GND, DACREF0.3V to (VAVDD3.3 + 0.3V)	DCLKP, DCLKN Continuous Current8mA
CLKP, CLKN to GND, DACREF0.3V to (VAVCLK + 0.3V)	Continuous Power Dissipation ($T_A = +70^{\circ}C$)
DAPO-DAP13, DBPO-DBP13,	256-Ball CSBGA
DCP0–DCP13 to GND, DACREF0.3V to (V _{DD1.8} + 0.3V)	(derate 38.6mW/°C above +70°C)
DDP0–DDP13, XORP, SYNCP,	Operating Temperature Range40°C to +85°C
PARP to GND, DACREF0.3V to (V _{DD1.8} + 0.3V)	Junction Temperature+150°C
DANO-DAN13, DBNO-DBN13,	Storage Temperature Range
DCN0–DCN13 to GND, DACREF0.3V to (V _{DD1.8} + 0.3V)	Soldering Temperature (reflow)+260°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS		MIN	ТҮР	MAX	UNITS
STATIC PERFORMANCE							
Resolution					14		Bits
Full-Scale Output Current Range	I _{OUT}	(Note 2)		10		80	mA
Output-Power Gain Error	GE			-0.7		+0.7	dB
Output Power Drift		Internal reference			-0.003		
Output-Power Drift		External reference			-0.0025		
Maximum Output Power	POUT	Differential, into 50 Ω	Differential, into 50Ω load, $f_{OUT} = 100MHz$		+9		dBm
Output Resistance	R _{OUT}	Differential			50		Ω
DYNAMIC PERFORMANCE	(Note 3)						
		DCLKDIV = 1, 2:1 m	iux mode	50		2300	
Clock Frequency Range	fCLK	DCLKDIV = 0, 2:1 m	iux mode	50		2200	MHz
		4:1 mux mode		50		2300	
		NR7 R7 RE modo	$1.8V \le (V_{DD}, V_{AVCLK}) \le 1.9V$	2300			
Output Undata Pata	f= + a		$1.7V \le (V_{DD}, V_{AVCLK}) \le 1.8V$	2200			Mana
	UAC	RFZ mode	4:1 mux mode only (f _{CLK} = f _{DAC} x 2)	1150			101505

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ELECTRICAL CHARACTERISTICS (continued)

PARAMETER	SYMBOL	С	ONDITIONS	MIN	TYP	MAX	UNITS
		f _{CLK} = 2300MHz, NRZ mode	f _{OUT} = 500MHz, -1dBFS		73		
Spurious-Free Dynamic	SEDD	f _{CLK} = 1500MHz, RZ mode	f _{OUT} = 1000MHz, -1dBFS		76		dDo
Range f _{OUT} ±200MHz	Srun	f _{CLK} = 2300MHz, RF mode	f _{OUT} = 1800MHz, -1dBFS		73		
		f _{CLK} = 1500MHz, RFZ mode	f _{OUT} = 1750MHz, -1dBFS		73		
			Adjacent channel power (750kHz from channel-block edge to 6MHz from channel- block edge)		-71	-62	
		$f_{OUT} = 400MHz,$ $f_{CLK} = 2048MHz,$ $T_J = +30^{\circ}C$ to +110°C, 2:1 mux mode	Next-adjacent channel power (6MHz from channel block edge to 12MHz from channel-block edge)		-72	-64	
			Third-adjacent channel power (12MHz from channel-block edge to 18MHz from channel-block edge)		-73	-66	
Noise and Spurious,			Noise in any other channel		-74		
Eight 6MHz QAM Channels, Average Total Power = -10dBFS	four = 860MHz, f _{CLK} = 2048MHz,		Adjacent channel rejection (750kHz from channel- block edge to 6MHz from channel-block edge)		-65		dBc
		f _{OUT} = 860MHz, f _{CLK} = 2048MHz, 2:1 mux mode	Next-adjacent channel rejection (6MHz from channel-block edge to 12MHz from channel- block edge)		-65		
			Third-adjacent channel rejection (12MHz from channel-block edge to 18MHz from channel block edge)		-65		
			Noise in any other channel		-65		1

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ELECTRICAL CHARACTERISTICS (continued)

PARAMETER	SYMBOL	CONDITIONS		MIN	ТҮР	MAX	UNITS	
DOCSIS DRFI Harmonic Distortion, Four 6MHz		f _{OUT} = 300MHz,	In each of eight 6MHz channels coinciding with 2nd harmonic components		-70		dPo	
QAM Channels, Average Total Power = -10dBFS		4:1 mux mode	In each of twelve 6MHz channels coinciding with 3rd harmonic components		-75		UBC	
DOCSIS DRFI Harmonic Distortion, Four 6MHz QAM		$f_{OUT} = 700MHz$,	In each of eight 6MHz channels coinciding with 2nd harmonic components		-68		dPo	
Channels, Average Total Power = -10dBFS		2:1 mux mode	In each of twelve 6MHz channels coinciding with 3rd harmonic components		-69		UDC	
		f _{CLK} = 2300MHz, NRZ mode	$f_{OUT1} = 500MHz$, -7dBFS, $f_{OUT2} = 501MHz$, -7dBFS		-78			
Two-Tone IMD	TTIMD	TTIMD	f _{CLK} = 1500MHz, RZ mode	$f_{OUT1} = 1000MHz, -7dBFS,$ $f_{OUT2} = 1001MHz, -7dBFS$		-69		dRo
		f _{CLK} = 2334.72MHz, RF mode	$f_{OUT1} = 1834 MHz, -12dBFS, f_{OUT2} = 1835 MHz, -12dBFS$		-71		UDC	
		f _{CLK} = 2300MHz, RFZ mode	$ f_{OUT1} = 2100 MHz, -12dBFS, $		-71			
4-Carrier ACLR for WCDMA, TM1, -18dBFS per Carrier at DAC Input	ACLR	f _{CLK} = 2334.72MHz, RF mode	$f_{OUT1} = 1952.5MHz, f_{OUT2} = 1957.5MHz, f_{OUT3} = 1962.5MHz, f_{OUT4} = 1967.5MHz$		67		dB	
Cain Elethood	C.E.	f _{CLK} = 2300MHz,	Over any single 6MHz channel		0.02		dP	
Gain Flathess	GF	$f_{OUT} \le 1000MHz$	Within 50MHz to 1000MHz band		3		UD	
		2:1 mux mode	f _{CLK} /4 spur		-90			
Clock Spurs			f _{CLK} /8 spur		-98		dBm	
		4:1 mux mode	t _{CLK} /4 spur		-75		-	
REFERENCE					-97			
Internal Reference Voltage Range	V _{REFIO}			1.1	1.2	1.3	V	
Reference Input-Voltage Compliance Range	V _{REFIOR}	(Note 4)		0.5		1.8	V	

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ELECTRICAL CHARACTERISTICS (continued)

PARAMETER	SYMBOL	CC	CONDITIONS		ТҮР	MAX	UNITS
Reference Input Resistance	R _{REFIO}				10		kΩ
Reference Voltage Drift	TCO _{REF}				50		ppm/°C
ANALOG OUTPUT TIMING							
Output Fall Time	t _{FALL}	90% to 10% (Note 5)			300		ps
Output Rise Time	t _{RISE}	10% to 90% (Note 5)			300		ps
Settling Time	t _S	Settling to 0.1% (Note	96)		26		ns
Output Bandwidth	t _{BW}	(Note 7)			2		GHz
Output Propagation Delay	t _{PD}	(Note 8)			1.5		ns
		DAP[13:0]/DAN[13:0]	to output		11.5		
Output Data Latanay	t	DBP[13:0]/DBN[13:0]	to output		12.5		Clock
	^I LAT	DCP[13:0]/DCN[13:0]	to output		13.5		cycles
		DDP[13:0]/DDN[13:0]	to output		14.5		
TIMING CHARACTERISTIC	S						- -
			DLLOFF = low, DELAY = high	1075		1150	
			DLLOFF = low, DELAY = open	950		1075	
			DLLOFF = open, DELAY = low	825		950	
		$f_{DLL} = f_{CLK}/22:1$	DLLOFF = open, DELAY = high	700		825	
		(MUX = 0)	DLLOFF = open, DELAY = open	625		700	
DLL Frequency Range	f _{DLL}		DLLOFF = resistor to ground, DELAY = low	550		625	MHz
			DLLOFF = resistor to ground, DELAY = high	475		550	
			DLLOFF = resistor to ground, DELAY = open	400		475	
		DLLOFF = resistor to ground, DELAY = low	550		575		
	$ t_{DLL} = t_{CLK}/4 4:1$ mux mode (MUX = 1)	DLLOFF = resistor to ground, DELAY = high	475		550		
			DLLOFF = resistor to ground, DELAY = open	400		475	

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ELECTRICAL CHARACTERISTICS (continued)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Data Skew	^t skew	Allowed skew of any LVDS input (DAP[13:0]/DAN[13:0], DBP[13:0]/DBN[13:0], DCP[13:0]/DCN[13:0], DDP[13:0]/DDN[13:0], XORP/ XOR, and PARP/PARN), with respect to the SYNC input; this parameter only applies when DLLOFF is not driven high (Note 9)	-310		+315	ps
Input Data to Clock Setup Time	^t SETUP	DLLOFF = 1.8V; data on the LVDS input pins must be stable for t_{SETUP} before the next edge of DCLKP/ DCLKN; this parameter only applies when DLLOFF is driven high, V_{MUX} = 0V (Note 9)	1.53			ns
Input Data to Clock Hold Time	^t hold	DLLOFF = 1.8V; data on the LVDS input pins must remain stable for t_{HOLD} after an edge of DCLKP/DCLKN; this parameter only applies when DLLOFF is driven high, $V_{MUX} = 0V$ (Note 9)	-0.9			ns
Parity Error Pulse Width	t _{ERR}	Pulse width of PERR when a parity error is detected		48		Data periods
Parity Pipeline Delay	^t PIPE,P	Pipeline delay in the internal parity calculation; delay the incoming PARP/PARN bit by this amount	3		3	Data periods
XOR Pipeline Delay	t _{PIPE,X}	Pipeline delay in the XOR path; delay the in coming XORP/XORN bit by this amount	1		1	Data periods
	UTS (DAP13		IO, DCP13	-DCP0,	DCN13-	DCN0,
Differential Input Logic-High			100			mV
Differential Input Logic-Low	VII				-100	mV
Input Common-Mode Voltage Range	V _{COM}		1.125		1.375	V
Differential Input Resistance	R _{IN}		85	107	125	Ω
Input Capacitance	C _{IN}			1.5		pF

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ELECTRICAL CHARACTERISTICS (continued)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
DIFFERENTIAL LOGIC INP DDP13-DDP0, DDN13-DDN	UTS (DAP13 NO, XORP, X	B-DAP0, DAN13-DAN0, DBP13-DBP0, DBN13-DBN ORN, PARP, PARN, SYNCP, SYNCN) SPECIFIED F	10, DCP1: OR DIFFE	B–DCP0, ERENTIA	DCN13–I L-HSTL I	DCN0, NPUT
Differential Input Logic-High	V _{IH(DC)}		160			mV
Differential Input Logic-Low	V _{IL(DC)}				-160	mV
Input Common-Mode Voltage Range	V _{COM}		0.456		1.0	V
Differential Input Resistance	R _{IN}		85	107	125	Ω
Input Capacitance	C _{IN}			1.5		рF
1.8V LVDS OUTPUTS (DCL	KP, DCLKN					
Differential Output	V _{DIFF,LVDS}	$V_{DIFF,LVDS} = V_{DCLKP} - V_{DCLKN}$, with 100 Ω differential termination	±250	±350	±450	mV
Output Rise and Fall Time	t _R , t _F	With 100Ω differential termination		0.3		ns
Common-Mode Voltage Range	V _{COM,LVDS}		1.125	1.28	1.375	V
DATA CLOCK RESET INPU	ITS (DCLKR	STP, DCLKRSTN)				
Differential Input Logic-High	V _{IH(RST)}		250			mV
Differential Input Logic-Low	V _{IL(RST)}				-250	mV
Input Common-Mode Voltage Range	V _{COM}		1.125		1.375	V
Differential Input Resistance	R _{IN}		85		125	Ω
Input Capacitance	C _{IN}			1.5		рF
Input Data to Clock Setup Time	^t SETUPRST	(Note 9)	0.3			ns
1.8V CMOS LOGIC INPUTS	(DCLKDIV,	MUX, RF, RZ, SE)				
Input Logic-High	V _{IH1.8}		0.7 x V _{DD1.8}			V
Input Logic-Low	V _{IL1.8}				0.3 x V _{DD1.8}	V
Input Leakage Current	I _{IN1.8}		-5		+5	μΑ
Input Capacitance	C _{IN1.8}			3		рF

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ELECTRICAL CHARACTERISTICS (continued)

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	MAX	UNITS		
1.8V 4-LEVEL LOGIC INPUTS (DELAY, DLLOFF)								
Input 4-Level Logic-High	V _{IH4}		27/32 x V _{DD1.8} + 50mV		V _{DD1.8}	V		
Input 4-Level Logic-Open	V _{OC4}		17/32 x V _{DD1.8} + 50mV		27/32 x V _{DD1.8} - 50mV	V		
Input 4-Level Logic-Res	V _{RC4}		7/32 x V _{DD1.8} + 50mV		17/32 x V _{DD1.8} - 50mV	V		
Input 4-Level Logic-Low	V _{IL4}		0		7/32 x V _{DD1.8} - 50mV	V		
Input Pullup Current	I _{PU4}		10	14.3	18.6	μA		
Input Pulldown Current	I _{PD4}		18.9	27	35.1	μA		
Input Capacitance	C _{IN4}			3		рF		
1.8V CMOS LOGIC OUTPU	TS (SO/LOC	K, PERR)						
Output Logic-High	V _{OH1.8}	I _{SOURCE} = 200µA	V _{DD1.8} - 0.2			V		
Output Logic-Low	V _{OL1.8}	I _{SINK} = 200μA			0.2	V		
CLOCK INPUTS (CLKP, CL	KN)							
Minimum Clock Input Power	P _{CLK,MIN}	(Note 10)		6		dBm		
Maximum Clock Input Power	P _{CLK,MAX}	Power measured into the MAX5879 clock input with 100 Ω external differential termination resistor		12		dBm		
Common-Mode Voltage Range	V _{COMCLK}	Input is self biased	Ň	AVCLK/	3	V		
Input Resistance	R _{CLK}	Differential		100		Ω		
Input Capacitance	C _{CLK}			2		pF		
POWER SUPPLIES								
Analog Supply Voltage Range	AV _{DD3.3}		3.2	3.3	3.5	V		
		$10MHz \le f_{CLK} \le 2200MHz$	1.7	1.8	1.9			
I.ov Supply voltage Hange	VDD1.8	$2200MHz \le f_{CLK} \le 2300MHz$	1.8		1.9	V		
Clock Supply Voltage		$10MHz \le f_{CLK} \le 2200MHz$	1.7	1.8	1.9	V		
Range	AVCLK	$2200MHz \le f_{CLK} \le 2300MHz$	1.8		1.9	v		

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ELECTRICAL CHARACTERISTICS (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, R_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = 1.8V, V_{DCLKDIV} = V_{DLLOFF} = V_{SE} = 0V,$ 2:1 mux mode, NRZ mode, R_{REFRES} = 500 Ω , transformer-coupled differential output, T_{A(MIN)} = -40°C to T_{J(MAX)} = +110°C, unless otherwise noted.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	MAX	UNITS
Analog Supply Current	I _{AVDD3.3}	$f_{CLK} = 2048MHz$, $f_{OUT} = 400MHz$, eight 6MHz QAM channels, average total power = -10dBFS		340	360	mA
1.8V Supply Current	IVDD1.8	f _{CLK} = 2048MHz, f _{OUT} = 400MHz, eight 6MHz QAM channels, average total power = -10dBFS		225	260	mA
Clock Supply Current	IAVCLK	$f_{CLK} = 2048MHz$, $f_{OUT} = 400MHz$, eight 6MHz QAM channels, average total power = -10dBFS		420	460	mA
		$f_{CLK} = 2048MHz$, $f_{OUT} = 400MHz$, eight 6MHz QAM channels, average total power = -10dBFS		2.3	2.5	
Power Dissipation	P _{DISS}	$ f_{CLK} = 2048MHz, f_{OUT} = 400MHz, eight 6MHz \\ QAM channels, full-scale current = 40mA, \\ average total output power = -16dBFS, \\ R_{REFRES} = 1k\Omega, R_{SET} = 4k\Omega $		1.8		W

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Ambient Temperature	T _A	(Note 11)	-40		+85	°C
Junction Temperature	ТJ		-40		+110	°C
Thermal Desistance		Air flow 0m/s		25.9		
Inermal Resistance,	θ _{JA}	Air flow 1m/s		23.1		°C/W
		Air flow 2.5m/s		21.9		
Thermal Resistance, Junction-to-Case	θ_{JC}			5.6		°C/W
Thermal Resistance, Junction-to-Board	θ_{JB}			15.9		°C/W
Thermal Characterization Parameter, Junction-to-Board	Ψ _{JB}			15		°C/W
Thermal Characterization Parameter, Junction-to-Top	Ψ _{JT}			1		°C/W

Note 1: All specifications are 100% tested at $T_J = +65^{\circ}$ C and $T_J = +110^{\circ}$ C to an accuracy of ±15°C, unless otherwise noted. Typical values are at $T_J = +65^{\circ}$ C ±15°C. Specifications at $T_J < +65^{\circ}$ C are guaranteed by design and characterization.

Note 2: Nominal full-scale current $I_{OUT} = 128 \times I_{REF}$.

Note 3: CLK input = +9dBm, AC-coupled sine wave.

Note 4: REFIO voltage less than 0.5V shuts down the internal clock circuitry of the device.

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Note 5: Measured single-ended into a double-terminated 50Ω load.

Note 6: From the application of a step at DAC input until corresponding DAC output is settled to the specified accuracy.

- **Note 7:** Measured differentially into a 50Ω load.
- Note 8: Referenced to rising edge of DAC update clock. Excludes data latency.
- **Note 9:** Guaranteed by design and characterization.
- Note 10: Transformer-coupled clock input (Figure 4).

Note 11: The package is mounted on a four-layer JEDEC standard test board, dissipating maximum power.

Typical Operating Characteristics

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, 2:1 mux mode, NRZ mode, \mathbf{R}_{REFRES} = 500\Omega$, transformer-coupled differential output, $T_A = +25^{\circ}C$, device soldered to the MAX5879 EV kit, unless otherwise noted.)

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Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V,$ 2:1 mux mode, NRZ mode, **R**_{REFRES} = 500 Ω , transformer-coupled differential output, T_A = +25°C, device soldered to the MAX5879 EV kit, unless otherwise noted.)

3000

2000

2500

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Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \textbf{R}_{SET} = 2k\Omega, V_{REFIO} = \text{external } 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, V_{DLOFF} = V_{SE} = 0V, V_{DLOFF} = V_{SE} = 0V, V_{DLOFF} = V_{SE} = 0V, V_{$ 2:1 mux mode, NRZ mode, R_{REFRES} = 500 Ω , transformer-coupled differential output, T_A = +25°C, device soldered to the MAX5879 EV kit, unless otherwise noted.)

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Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, V_{SE} =$ 2:1 mux mode, NRZ mode, R_{REFRES} = 500 Ω , transformer-coupled differential output, T_A = +25°C, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 2.14GHz, SPAN = 53.84MHz, RBW = 30kHz, VBW = 300kHz, SWEEP = 2s

CENTER = 2.14GHz, SPAN = 68.84MHz, RBW = 30kHz, VBW = 300kHz, SWEEP = 2s

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, 2:1 mux mode, NRZ mode, R_{REFRES} = 500\Omega$, transformer-coupled differential output, $T_A = +25^{\circ}C$, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 2.14GHz, SPAN = 1GHz, RBW = 30kHz, VBW = 3kHz, SWEEP = 11.3s (1001pts)

MARKER	SIGNAL	FREQUENCY (GHz)	POWER (dBm)
1	IMAGE, 2ND NYQUIST	2.139	-30.18
2	IMAGE, 3RD NYQUIST	2.530	-33.09
3	CLOCK	2.335	-41.92
4	HD2, 2ND NYQUIST	1.945	-99.12
5	HD3, 2ND NYQUIST	1.751	-97.63

CENTER = 2.14GHz, SPAN = 1GHz, RBW = 30kHz, VBW = 3kHz, SWEEP = 11.3s (1001pts)

MARKER	SIGNAL	FREQUENCY (GHz)	POWER (dBm)
1	CH 4 IMAGE, 2ND NYQUIST	2.132	-36.25
2	CH 1 IMAGE, 2ND NYQUIST	2.148	-36.51
3	CH 1 IMAGE, 3RD NYQUIST	2.523	-39.20
4	CH 4 IMAGE, 3RD NYQUIST	2.538	-39.14
5	CLOCK	2.335	-42.43

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, 2:1 mux mode, NRZ mode, \mathbf{R}_{REFRES} = 500\Omega$, transformer-coupled differential output, $T_A = +25^{\circ}C$, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 940.5MHz, SPAN = 20MHz

1	TOTAL POWER REF		-1.66dBm/0.4MHz		I OWFR	<- PEAK -> LIPPE		LIPPER	R	
_	START FREQ	STOP FREQ	INTEG BW	dBc	$\Delta LIM(dB)$	FREQ (Hz)	dBc	$\Delta LIM(dB)$	FREQ (Hz)	
ſ	200.0kHz	400.0kHz	30.00kHz	-42.53	(-12.53)	-200.0k	-41.41	(-11.41)	202.0k	
	400.0kHz	600.0kHz	30.00kHz	-79.86	(-19.86)	-400.0k	-77.46	(-17.46)	400.0k	
	600.0kHz	1.200MHz	30.00kHz	-92.37	(-22.37)	-610.0k	-91.74	(-21.74)	690.0k	
	1.200MHz	1.800MHz	30.00kHz	-90.85	(-17.85)	-1.570M	-89.03	(-16.03)	1.330M	
	1.800MHz	6.000MHz	30.00kHz	-90.77	(-10.77)	-3.550M	-90.29	(-10.29)	5.410M	
	6.000MHz	10.00MHz	30.00kHz	-91.65	(-6.65)	-8.120M	-90.37	(-5.37)	7.090M	

REF -6.00dBm

4-CARRIER GSM (fclk = 2.33472GHz, fcenter = 940MHz, RZ MODE)

CENTER = 940.450MHz, SPAN = 12MHz, RBW = 30kHz, VBW = 3kHz, SWEEP = 2s (1001pts)

MARKER	POWER	MARKER	POWER
1	-17.36dBm	6	(Δ) -74.11dB
2	-17.20dBm	7	(Δ) -78.54dB
3	-17.43dBm	8	(Δ) -79.01dB
4	-17.32dBm	9	(Δ) -78.73dB
5	(Δ) -70.48dB	10	(Δ) -78.75dB

10dB/div LOG

> -16 -26

14-Bit, 2.3Gsps Direct RF Synthesis DAC with **Selectable Frequency Response**

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, V_{SE} =$ 2:1 mux mode, NRZ mode, R_{REFRES} = 500 Ω , transformer-coupled differential output, T_A = +25°C, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 1.26GHz, SPAN = 489.2MHz, RBW = 30kHz, VBW = 3kHz, SWEEP = 2s

8-CARRIER 8 PSK, 28.86MBd, 38.36MHz SPACING (fclk = 2.02GHz, fcenter = 1.26GHz, 3rd NYQUIST ZONE, RFZ MODE) 10dB/div LOG REF -33.00dBm -43 •2∆1 ۵ -53 -63 3Δ1 -73 -83 4Δ1 -93 -103 www.wopyW while a first white a section of A deres White The White -113 -123

CENTER = 1.2598GHz, SPAN = 650MHz, RBW = 30kHz, VBW = 3kHz, SWEEP = 2s (1001pts)

MARKER	FREQUENCY	POWER
1	1.3758GHz	-52.53dBm
2	(Δ) -267.0MHz	(Δ) -1.01dB
3	(Δ) -365.4MHz	(Δ) -20.68dB
4	(Δ) 139.7MHz	(Δ) -46.92dB

14-Bit, 2.3Gsps Direct RF Synthesis DAC with **Selectable Frequency Response**

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \textbf{R}_{SET} = 2k\Omega, V_{REFIO} = \text{external } 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, V_{DLOFF} = V_{SE} = 0V, V_{DLOFF} = V_{SE} = 0V, V_{DLOFF} = V_{SE} = 0V, V_{$ 2:1 mux mode, NRZ mode, R_{REFRES} = 500 Ω , transformer-coupled differential output, T_A = +25°C, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 2.348GHz, SPAN = 180MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 44.69s

CENTER = 550MHz, SPAN = 1.1GHz, RBW = 6MHz, VBW = 620kHz, SWEEP = 2s (1001pts)

MARKER	SIGNAL	FREQUENCY (MHz)	POWER
1	fout	99.0	-3.23dBm
2	HD5	(Δ) 397.1	(Δ) -72.78dB
3	HD2	(Δ) 99.0	(Δ) -73.63dB
4	HD3	(Δ) 198.0	(Δ) -74.49dB
5	HD9	(Δ) 198.0	(Δ) -71.35dB

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, 2:1 mux mode, NRZ mode, R_{REFRES} = 500\Omega$, transformer-coupled differential output, $T_A = +25^{\circ}C$, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 550MHz, SPAN = 1.1GHz, RBW = 6MHz, VBW = 620kHz, SWEEP = 2s (1001pts)

MARKER	SIGNAL	FREQUENCY (MHz)	POWER
1	fout	302.5	-3.31dBm
2	HD2	(Δ) 303.6	(Δ) -67.77dB
3	HD5	(Δ) 224.4	(Δ) -72.92dB
4	HD3	(Δ) 603.9	(Δ) -71.11dB
5	HD7	(Δ) -226.6	(Δ) -74.63dB

MARKER	SIGNAL	FREQUENCY (MHz)	POWER
1	fout	903.1	-6.93dBm
2	HD3	(Δ) -242.0	(Δ) -66.97dB
3	HD2	(Δ) -662.2	(Δ) -64.91dB
4	HD5	(Δ) -486.2	(Δ) -70.08dB
5		(Δ) -782.1	(Δ) -70.21dB

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, 2:1 mux mode, NRZ mode, R_{REFRES} = 500\Omega$, transformer-coupled differential output, $T_A = +25^{\circ}C$, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 550MHz, SPAN = 1.1GHz, RBW = 6MHz, VBW = 620kHz, SWEEP = 2s (1001pts)

MARKER	SIGNAL	FREQUENCY (MHz)	POWER
1	fout	99.0	-10.43dBm
2	HD5	(Δ) 410.3	(Δ) -69.56dB
3	HD2	(Δ) 105.6	(Δ) -70.14dB
4	HD3	(Δ) 202.4	(Δ) -70.93dB
5	HD9	(Δ) 773.3	(Δ) -69.10dB

MARKE	ER	SIGNAL	FREQUENCY (MHz)	POWER
1		fout	291.5	-11.11dBm
2		HD2	(Δ) 308.0	(Δ) -66.47dB
3			(Δ) -225.5	(Δ) -70.45dB
4			(Δ) 218.9	(Δ) -70.00dB
5			(A) 605	(Δ) -68.09dB

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, 2:1 mux mode, NRZ mode, \mathbf{R}_{REFRES} = 500\Omega$, transformer-coupled differential output, $T_A = +25^{\circ}C$, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 550MHz, SPAN	= 1.1GHz, RBW :	= 6MHz, VBW =	620kHz, S	WEEP = $2s$ (1001pts)
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MARKER	SIGNAL	FREQUENCY (MHz)	POWER
1	fout	892.1	-14.99dBm
2		(Δ) -243.1	(Δ) -66.47dB
3	HD2	(Δ) -644.6	(Δ) -64.13dB
4		(Δ) -491.7	(Δ) -67.08dB
5		(Δ) -19.8	(Δ) -66.78dB

MARKER	SIGNAL	FREQUENCY (MHz)	POWER
1	fout	117.7	-14.04dBm
2	HD5	(Δ) 389.4	(Δ) -67.86dB
3	HD2	(Δ) 90.2	(Δ) -68.59dB
4		(Δ) 198.0	(Δ) -68.95dB
5		(Δ) 673.2	(Δ) -67.58dB

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, 2:1 mux mode, NRZ mode, \mathbf{R}_{REFRES} = 500\Omega$, transformer-coupled differential output, $T_A = +25^{\circ}C$, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 550MHz, SPAN = 1.1GHz, RBW = 6MHz, VBW = 620kHz, SWEEP = 2s (1001pts)

MARKER	SIGNAL	FREQUENCY (MHz)	POWER
1	fout	284.9	-14.41dBm
2	HD2	(Δ) 317.9	(Δ) -65.28dB
3		(Δ) -168.3	(Δ) -68.82dB
4		(Δ) 212.3	(Δ) -67.31dB
5	HD3	(Δ) 559.9	(Δ) -66.06dB

CENTER = 550MHz, SPAN = 1.1GHz, RBW = 6MHz, VBW = 620kHz, SWEEP = 2s (1001pts)

MARKER	SIGNAL	FREQUENCY (MHz)	POWER	
1	fout	891.0	-17.98dBm	
2	HD2	(Δ) -654.7	(Δ) -62.80dB	
3		(Δ) -264.0	(Δ) -63.69dB	
4		(Δ) -79.2	(Δ) -63.80dB	
5	f _{CLK} /2	(Δ) 133.1	(Δ) -61.40dB	

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, 2:1 mux mode, NRZ mode, R_{REFRES} = 500\Omega$, transformer-coupled differential output, $T_A = +25^{\circ}C$, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 550MHz, SPAN = 1.1GHz, RBW = 6MHz, VBW = 620kHz, SWEEP = 2s (1001pts)

MARKER	SIGNAL	FREQUENCY (MHz)	POWER	
1	fout	100.0	-20.87dBm	
2	fout	(Δ) 132.0	(Δ) -0.21dB	
3		(Δ) 410.3	(Δ) -62.01dB	
4		(Δ) 712.8	(Δ) -62.00dB	
5	f _{CLK} /2	(Δ) 922.9	(Δ) -59.98dB	

CENTER = 550MHz, SPAN = 1.1GHz, RBW = 6MHz, VBW = 620kHz, SWEEP = 2s (1001pts)

MARKER SIGNAL F		FREQUENCY (MHz)	POWER
1	1 four 23		-20.93dBm
2	fout	(Δ) 179.3	(Δ) -0.52dB
3		(Δ) -121.0	(Δ) -61.92dB
4		(Δ) 579.7	(Δ) -61.46dB
5	f _{CLK} /2	(Δ) 789.8	(Δ) -60.18dB

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, 2:1 mux mode, NRZ mode, \mathbf{R}_{REFRES} = 500\Omega$, transformer-coupled differential output, $T_A = +25^{\circ}C$, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 550MHz, SPAN = 1.1GHz, RBW = 6MHz, VBW = 620kHz, SWEEP = 2s (1001pts)

MARKER	ER SIGNAL FREQUENCY (MI		POWER	
1	fout	795.3	-23.65dBm	
2	fout	(Δ) 183.7	(Δ) -1.65dB	
3		(Δ) -284.9	(Δ) -58.79dB	
4		(Δ) -636.9	(Δ) -59.45dB	
5	f _{CLK} /2	(Δ) 226.6	(Δ) -56.82dB	

CENTER = 550MHz, SPAN = 1.1GHz, RBW = 6MHz, VBW = 620kHz, SWEEP = 2s (1001pts)

MARKER	MARKER SIGNAL FREQUENCY (MH		POWER	
1	fout	118.8	-24.49dBm	
2	fout	(Δ) 363.0	(Δ) -1.18dB	
3		(Δ) -70.4	(Δ) -58.93dB	
4		(Δ) 717.2	(Δ) -58.07dB	
5	f _{CLK} /2	(Δ) 903.1	(Δ) -56.87dB	

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, R_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V,$ 2:1 mux mode, NRZ mode, R_{REFRES} = 500 Ω , transformer-coupled differential output, T_A = +25°C, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 550MHz, SPAN = 1.1GHz, RBW = 6MHz, VBW = 620kHz, SWEEP = 2s (1001pts)

MARKER	SIGNAL	FREQUENCY (MHz)	POWER	
1	fout	513.7	-25.17dBm	
2	fout	(Δ) 372.9	(Δ) -2.77dB	
3		(Δ) -324.5	(Δ) -58.06dB	
4		(Δ) -57.2	(Δ) -57.84dB	
5	f _{CLK} /2	(Δ) 510.4	(Δ) -55.40dB	

CENTER = 550GHz, SPAN = 1.1GHz, RBW = 6MHz, VBW = 620kHz, SWEEP = 2s (1001pts)

MARKER	SIGNAL	FREQUENCY (MHz)	POWER	
1	fout	177.1	-26.9dBm	
2	fout	(Δ) 745.8	(Δ) -4.40dB	
3		(Δ) -97.9	(Δ) -56.35dB	
4	f _{CLK} /2	(Δ) 845.9	(Δ) -53.78dB	

14-Bit, 2.3Gsps Direct RF Synthesis DAC with **Selectable Frequency Response**

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \textbf{R}_{\textbf{SET}} = 2\textbf{k}\Omega, V_{REFIO} = \text{external } 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, V_{DCLKDIV} = 1.8V, V_{DCLKDIV} =$ 2:1 mux mode, NRZ mode, R_{REFRES} = 500 Ω , transformer-coupled differential output, T_A = +25°C, device soldered to the MAX5879 EV kit, unless otherwise noted.)

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	CENTER = 1.2	5GHz, SPAN = 2	2.5GHz, RBW =	6MHz, VBW = 6	20kHz, SWEEP	= 2s (1001pts)			

MARKER	SIGNAL	FREQUENCY	POWER
1	fout	297.5MHz	-11.19dBm
2	IMAGE, 2ND NYQUIST	(Δ) 1.4425GHz	(Δ) -16.93dB
3	IMAGE, 3RD NYQUIST	(Δ) 2.0575GHz	(Δ) -31.13dB
4	fclk	2.0475GHz	-31.62dBm
5		(Δ) 1.1491GHz	(Δ) -67.03dB
6		(Δ) 302.5GHz	(Δ) -67.35dB
7		(Δ) 602.5GHz	(Δ) -68.88dB
8	f _{CLK} /2	1.0225GHz	-80.99dBm
9	3 x f _{CLK} /2	1.5350GHz	-81.51dBm

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, 2:1 mux mode, NRZ mode, \mathbf{R}_{REFRES} = 500\Omega$, transformer-coupled differential output, $T_A = +25^{\circ}C$, device soldered to the MAX5879 EV kit, unless otherwise noted.)

MARKER	SIGNAL	FREQUENCY	POWER
1	fout	892.5MHz	-11.19dBm
2	IMAGE, 2ND NYQUIST	(Δ) 247.5MHz	(Δ) -2.72dB
3	fclk	2.0475GHz	-31.56dBm
4		(Δ) 905.0MHz	(Δ) -64.83dB
5		(Δ) 506.6MHz	(Δ) -68.15dB
6		(Δ) -647.5MHz	(Δ) -64.24dB
7		(Δ) -245.0MHz	(Δ) -66.59dB
8	f _{CLK} /2	1.0225GHz	-80.47dBm
9	3 x f _{CLK} /2	1.5350GHz	-81.71dBm

CENTER = 1.25GHz, SPAN = 2.5GHz, RBW = 6MHz, VBW = 620kHz, SWEEP = 2s (1001pts)

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V,$ 2:1 mux mode, NRZ mode, **R**_{REFRES} = 500 Ω , transformer-coupled differential output, T_A = +25°C, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 99MHz, SPAN = 42MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

CENTER = 303MHz, SPAN = 42MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

CENTER = 903MHz, SPAN = 42MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

14-Bit, 2.3Gsps Direct RF Synthesis DAC with **Selectable Frequency Response**

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, V_{SE} =$ 2:1 mux mode, NRZ mode, R_{REFRES} = 500 Ω , transformer-coupled differential output, T_A = +25°C, device soldered to the MAX5879 EV kit, unless otherwise noted.)

4-CHANNEL 256 QAM (DOCSIS, ANNEX B) (fclk = 2.048GHz, fcenter = 102MHz)

CENTER = 102MHz, SPAN = 60MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

4-CHANNEL 256 QAM (DOCSIS, ANNEX B) (fclk = 2.048GHz, fcenter = 300MHz)

CENTER = 300MHz, SPAN = 60MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

CENTER = 900MHz, SPAN = 60MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, 2:1 mux mode, NRZ mode, R_{REFRES} = 500\Omega$, transformer-coupled differential output, $T_A = +25^{\circ}C$, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 102MHz, SPAN = 84MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

CENTER = 300MHz, SPAN = 84MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

8-CHANNEL 256 QAM (DOCSIS, ANNEX B) (fclk = 2.048GHz, fcenter = 900MHz)

CENTER = 900MHz, SPAN = 84MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, 2:1 mux mode, NRZ mode, R_{REFRES} = 500\Omega$, transformer-coupled differential output, $T_A = +25^{\circ}C$, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 78MHz, SPAN = 84MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

CENTER = 396MHz, SPAN = 84MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

32-CHANNEL 256 QAM (DOCSIS, ANNEX B) (fclk = 2.048GHz, fcenter = 888MHz, WORST-CASE SIDE)

CENTER = 960MHz, SPAN = 84MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, 2:1 mux mode, NRZ mode, \mathbf{R}_{REFRES} = 500\Omega$, transformer-coupled differential output, $T_A = +25^{\circ}C$, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 468MHz, SPAN = 84MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

CENTER = 870MHz, SPAN = 84MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

CENTER = 912MHz, SPAN = 84MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

14-Bit, 2.3Gsps Direct RF Synthesis DAC with **Selectable Frequency Response**

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 4k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, V_{DCLKDIV} = 1.8V, V_{DCLKDIV}$ 2:1 mux mode, NRZ mode, R_{REFRES} = $1k\Omega$, transformer-coupled differential output, T_A = +25°C, device soldered to the MAX5879 EV kit, unless otherwise noted.)

MARKER	SIGNAL	FREQUENCY (MHz)	POWER
1	fout	86.9	-20.21dBm
2		(Δ) 126.5	(Δ) -66.33dB
3		(Δ) 420.2	(Δ) -65.75dB
4		(Δ) 724.9	(Δ) -64.88dB
5	f _{CLK} /2	(Δ) 937.2	(Δ) -60.82dB

MARKER	SIGNAL	FREQUENCY (MHz)	POWER
1	fout	279.6	-20.59dBm
2		(Δ) 325.6	(Δ) -62.61dB
3		(Δ) 228.8	(Δ) -65.38dB
4		(Δ) 532.4	(Δ) -64.16dB
5	fclk/2	(Δ) 744.7	(Δ) -60.16dB

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 4k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V,$ 2:1 mux mode, NRZ mode, **R**_{REFRES} = 1k Ω , transformer-coupled differential output, T_A = +25°C, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 550MHz	, SPAN = 1.1GHz	, RBW = 6MHz,	VBW = 620kHz,	SWEEP = 2	2s (1001pts)
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MARKER	SIGNAL	FREQUENCY (MHz)	POWER
1	fout	891.0	-24.04dBm
2		(Δ) -641.3	(Δ) -60.82dB
3		(Δ) -383.9	(Δ) -61.55dB
4		(Δ) -79.2	(Δ) -61.01dB
5	f _{CLK} /2	(Δ) 133.1	(Δ) -57.11dB

8-CHANNEL 256 QAM (DOCSIS, ANNEX B) (fclk = 2.048GHz, fcenter = 102MHz, Ifull-scale = 40mA, Iconst = 20mA)

CENTER = 102MHz, SPAN = 84MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 4k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V,$ 2:1 mux mode, NRZ mode, **R**_{REFRES} = 1k Ω , transformer-coupled differential output, T_A = +25°C, device soldered to the MAX5879 EV kit, unless otherwise noted.)

CENTER = 300MHz, SPAN = 84MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

8-CHANNEL 256 QAM (DOCSIS, ANNEX B) (fclk = 2.048GHz, fcenter = 900MHz, Ifull-scale = 40mA, Iconst = 20mA)

CENTER = 900MHz, SPAN = 84MHz, RBW = 10kHz, VBW = 1kHz, SWEEP = 2s

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Typical Operating Characteristics (continued)

 $(V_{AVDD3.3} = 3.3V, V_{DD1.8} = V_{AVCLK} = 1.8V, \mathbf{R}_{SET} = 2k\Omega, V_{REFIO} = external 1.25V, V_{DELAY} = V_{DCLKDIV} = 1.8V, V_{DLLOFF} = V_{SE} = 0V, 2:1 mux mode, NRZ mode,$ **R** $_{REFRES} = 500\Omega, transformer-coupled differential output, T_A = +25°C, device soldered to the MAX5879 EV kit, unless otherwise noted.)$

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Ball Configurations

Ball Assignments (DAC Outputs, Power Supplies, Reference, and DAC Clock)

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Ball Configurations (continued)

Ball Assignments (Data Connections, 4:1 Mux Mode)

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Ball Configurations (continued)

Ball Assignments (Data Connections, 2:1 Mux Mode)

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Ball Configurations (continued)

Ball Assignments (Data Connections, RFZ Mode)

14-Bit, 2.3Gsps Direct RF Synthesis DAC with Selectable Frequency Response

Ball Description

BALL	NAME	FUNCTION					
A1	CREF	Noise Bypass Pin. A 1 μ F capacitor between the CREF and DACREF band limits the phase noise of the DAC.					
A2	DACREF	Current-Set Resistor Return Path. For an 80mA full-scale output current, connect a $2k\Omega$ resistor between FSADJ and DACREF. DACREF is internally connected to GND. Do not connect to external ground.					
A3	REFIO	Reference Input/Output. Output pin for the internal 1.2V bandgap reference. REFIO has a $10k\Omega$ series resistance and can be driven using an external reference. Connect a 1μ F capacitor between REFIO and DACREF.					
A4	FSADJ	Full-Scale Adjust Input. Sets the full-scale output current of the DAC. For an 80mA full-scale output current, connect a $2k\Omega$ resistor between FSADJ and DACREF. See the <i>Reference System</i> section for details.					
A5	REFRES	Connect a resistor between REFRES and $AV_{DD3.3}$ to set the standing current (I _{CONST}). For 80mA full-scale output current, connect a 500 Ω resistor between REFRES and $AV_{DD3.3}$ (I _{CONST} = I _{FULLSCALE} /2). See the <i>Reference System</i> section for details.					
A6, A8, A9, A12, A13, B8, B9, B12, B13	AV _{DD3.3}	Analog 3.3V Supply Voltage. Connect 0.1 μF bypass capacitors between each AV_{DD3.3} ball and GND.					
A7, A14, A15, A16, B1–B7, B14, C6–C14, D6–D14, E1, E6–E14, F1–F16, G5–G16, H9–H12, L5–L8, M13, M14, T1–T4, T13–T16	GND	Analog Ground. Connect to ground plane with minimum inductance.					
A10, B10	OUTN	Negative Terminal of Differential DAC Output. OUTN has an internal 25Ω resistor to AV _{DD3.3} .					
A11, B11	OUTP	Positive Terminal of Differential DAC Output. OUTP has an internal 25Ω resistor to AV _{DD3.3} .					
B15, B16, C15, D15, E15, E16	AV _{CLK}	Clock 1.8V Supply Voltage. Connect 0.1 μF bypass capacitors between each AV $_{\text{CLK}}$ ball and GND.					
C1–C5, G1–G4, H13–H16	V _{DD1.8}	1.8V Supply Voltage. Connect 0.1μ F bypass capacitors between each V _{DD1.8} ball and GND.					
C16	CLKN	Negative Converter Clock Input. There is an internal 100Ω termination resistor between CLKP and CLKN.					

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Ball Description (continued)

BALL	NAME	FUNCTION				
D1	SE	Scan Enable Input. During normal operation, SE should be connected to GND. When SE is high (1.8V), the parallel input register is configured as a shift register, allowing the contents of the input register to be shifted out on SO/LOCK. Note: Scan mode does not operate in 2:1 or RFZ modes. SE is a 3.3V tolerant, 1.8V CMOS input with an internal pulldown resistor.				
D2	SO/LOCK	1.8V CMOS Logic Output SE = High: SO/LOCK is a scan data output. SE = Low: SO/LOCK is a DLL locking indicator output, and logic-high indicates DLL is locked.				
D3	PERR	1.8V CMOS Logic-Level Parity Error Output. When a parity error is detected in the DAC input data, this pin is set high for a minimum of 48 LVDS data periods. This can be used to provide failure monitoring for the system. Note that this pin can pulse high when the power is initially applied and before the DLL is locked.				
D4	MUX	 MUX Mode Selection MUX = 0: Input data format in 2:1 (ports B and C). MUX = 1: Input data format in 4:1 for NRZ, RZ, and RF modes. Input data format 2:1 (ports A and C) for RFZ mode. MUX is a 3.3V tolerant, 1.8V CMOS input with an internal pulldown resistor. 				
D5	DELAY	 Data Clock Mode Control DELAY = 0: No clock delay when DLLOFF = 1. DELAY = 1: One f_{CLK} period delay added to DCLKP/DCLKN when DLLOFF = 1. DLLOFF ≠ 1: DELAY is a 4-level input pin used along with the DLLOFF pin (see Table 1 for details). DELAY is a 3.3V tolerant, 1.8V 4-level-logic input. 				
D16	CLKP	Positive Converter Clock Input. There is an internal 100Ω termination resistor between CLKP and CLKN.				
E2	DCLKDIV	Data Clock Divider Mode Input DCLKDIV = 1: DCLKP/DCLKN is $f_{CLK}/4$ when MUX = 0, $f_{CLK}/8$ when MUX = 1. DCLKDIV = 0: DCLKP/DCLKN is $f_{CLK}/2$ when MUX = 0, $f_{CLK}/4$ when MUX = 1. DCLKDIV is a 3.3V tolerant, 1.8V CMOS input with an internal pulldown resistor.				
E3	RZ	Return-to-Zero (RZ) Mode-Select Input RZ = 0 (and RF = 0): NRZ DAC operation. RZ = 1 (and RF = 0): RZ DAC operation. RZ = 1 (and RF = 1, MUX = 1): RFZ DAC operation. RZ is a 3.3V tolerant, 1.8V CMOS input with an internal pulldown resistor.				
E4	DLLOFF	 Data Clock Mode Control DLLOFF ≠ 1: DLL is enabled as a 4-level-logic input pin used along with the DELAY pin (see Table 1 for details). DLLOFF = 1: DLL is disabled. Reset DLL after a stable clock is applied. Set DLLOFF = 1 to perform the reset. DLLOFF is a 3.3V tolerant, 1.8V 4-level-logic input. 				

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Ball Description (continued)

BALL	NAME	FUNCTION				
E5	RF	Radio Frequency (RF) Mode-Select Input RF = 0: NRZ or RZ mode. RF = 1 (and RZ = 0): RF mode. RF = 1 (and RZ = 0, MUX = 1): RFZ mode. RF is a 3.3V tolerant, 1.8V CMOS input with an internal pulldown resistor.				
H1, H3, H5, H7, J1, J3, J5, J7, K1, K3, K5, K7, L1, L3	DAP[13:0]	Positive Terminals of the A-Channel LVDS Data Inputs (Offset Binary Format). DAP13 is the MSB. Connect to GND if only using 2:1 mux mode.				
H2, H4, H6, H8, J2, J4, J6, J8, K2, K4, K6, K8, L2, L4	DAN[13:0]	Negative Terminals of the A-Channel LVDS Data Inputs. Connect to GND if only using 2:1 mux mode.				
J9, J11, J13, J15, K9, K11, K13, K15, L9, L11, L13, L15, M9, M11	DDP[13:0]	Positive Terminals of the D-Channel LVDS Data Inputs (Offset Binary Format). DDP13 is the MSB. Connect to GND if using only 2:1 mux mode or RFZ mode.				
J10, J12, J14, J16, K10, K12, K14, K16, L10, L12, L14, L16, M10, M12	DDN[13:0]	Negative Terminals of the D-Channel LVDS Data Inputs. Connect to GND if using only 2:1 MUX mode or RFZ mode.				
M1, M3, M5, M7, N1, N3, N5, N7, P1, P3, P5, P7, R1, R3	DBP[13:0]	Positive Terminals of the B-Channel LVDS Data Inputs (Offset Binary Format). DBP13 is the MSB. Connect to GND if only using RFZ mode.				
M2, M4, M6, M8, N2, N4, N6, N8, P2, P4, P6, P8, R2, R4	DBN[13:0]	Negative Terminals of the B-Channel LVDS Data Inputs. Connect to GND if only using RFZ mode.				
M15	DCLKRSTP	Positive Terminal of the LVDS Input for DCLK Reset				
M16	DCLKRSTN	Negative Terminal of the LVDS Input for DCLK Reset				
N9, N11, N13, N15, P9, P11, P13, P15, R9, R11, R13, R15, T9, T11	DCP[13:0]	Positive Terminals of the C-Channel LVDS Data Inputs (Offset Binary Format). DCP13 is the MSB.				

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Ball Description (continued)

BALL	NAME	FUNCTION				
N10, N12, N14, N16, P10, P12, P14, P16, R10, R12, R14, R16, T10, T12	DCN[13:0]	Negative Terminals of the C-Channel LVDS Data Inputs				
R5	PARP	Positive Terminal of the Parity LVDS Data Input. The parity input data is used internally to provide detection of bit errors between the data source and the DAC and can be used for system monitoring. PARP/PARN should be delayed three DCLKP/DCLKN cycles.				
R6	PARN	Negative Terminal of the Parity LVDS Data Input				
R7	SYNCP	Positive Terminal of the Synchronization LVDS Data Input. The SYNCP/SYNCN pair should be driven synchronously with the DAC data input pairs and should be a pseudorandom sequence.				
R8	SYNCN	Negative Terminal of the Synchronization LVDS Data Input				
T5	DCLKP	Positive Terminal of the LVDS Data Clock Output				
T6	DCLKN	Negative Terminal of the LVDS Data Clock Output				
Τ7	XORP	Positive Terminal of the XOR LVDS Data Input. The A-, B-, C-, and D-channel data bits are all logically exclusive ORed by the data on the XOR pin internally. This function can be used for whitening spurious signals that can be present in the input data. XORP/XORN should be delayed one DCLKP/DCLKN cycle. To disable the XOR function, drive logic 0 into the XORP/XORN input pair.				
Т8	XORN	Negative Terminal of the XOR LVDS Data Input				

General Description

The MAX5879 is a high-performance, 14-bit, 2.3Gsps multi-Nyquist digital-to-analog converter (DAC). The device accepts a clock signal up to 2.3GHz and provides four selectable frequency-response modes (NRZ, RZ, RF, and RFZ). The high sample rate and selectable response allow digital generation of signals to more than 2GHz output frequency.

The device has four 14-bit, multiplexed, low-voltage differential signaling (LVDS) input ports and includes a DCLK output for synchronization with the data source, as well as SYNC and parity input bits. The data interface operates in either single data-rate or double data-rate mode and in 2:1 or 4:1 multiplexed (mux) mode. The 2:1 mux mode reduces the number of pins from the driving data source (FPGA or ASIC). An integrated delay-locked loop (DLL) circuit is also included to ease data synchronization and timing requirements with the data source. The parity input and parity error flag output can be used to detect bit errors between the data source and the

DAC. A DCLK reset circuit is included for aligning the data-capture clocks of multiple DACs.

The device is a current-steering DAC with an integrated, 50Ω differential output termination to ensure optimum dynamic performance. The device produces a user-defined (R_{SET}, R_{REFRES}), full-scale current range up to 80mA, providing high output power.

Operating from 1.8V and 3.3V power supplies, the device dissipates 2.4W at 2.3Gsps. The device is specified over the -40°C to +85°C extended temperature range and is offered in a 256-ball CSBGA package.

Reference System

The device supports operation with the on-chip 1.2V bandgap reference or an external reference voltage source. REFIO serves as the input for an external low-impedance reference source, or as the output if the DAC is operating with the internal reference. For stable operation with the internal reference, decouple REFIO to DACREF with a 1µF capacitor. Since REFIO has a 10k Ω series resistance, buffer REFIO with an external amplifier to drive external loads.

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The device's reference circuit (Figure 1) employs a control amplifier, designed to regulate the full-scale current (I_{OUT}) for the differential current outputs of the DAC. The bandwidth of the control amplifier is typically less than 100kHz. The DAC full-scale output current can be calculated as follows:

 $I_{OUT} = 128 \times I_{REF}$

Figure 1. Reference Architecture, Internal Reference Configuration

where I_{REF} is the reference output current ($I_{REF} = V_{REFIO}/R_{SET}$) and I_{OUT} is the full-scale output current of the DAC.

The device also produces a constant standing current at the DAC outputs. This constant current should be set to 1/2 of the full-scale current with a maximum value of 40mA. A resistor connected between REFRES and AV_{DD3.3} (R_{REFRES} in Figure 1) is used to set the value of the constant current (I_{CONST}). The current from REFRES is regulated to produce a 0.5V drop across R_{REFRES} and is scaled by a factor of 40 to produce the constant DAC output current. To determine the required R_{REFRES} value for a specific current, use the following formula:

$R_{REFRES} = 40 \times 0.5 V / I_{CONST}$

where R_{REFRES} is the required resistor value, and I_{CONST} is 1/2 of the full-scale output current of the DAC.

With an external reference voltage of 1.25V, R_{SET} is typically set to $2k\Omega$ and R_{REFRES} is set to 500Ω , resulting in a full-scale signal current of 80mA and a constant current of 40mA, which produces a maximum continuous-wave (CW) output power of 9dBm. In general, the dynamic performance of the DAC improves with increasing full-scale current. Total power dissipation can be reduced at the expense of dynamic performance by lowering the full-scale and constant-current settings. For example, by reducing the full-scale current to 40mA and the constant current to 20mA, the power dissipation drops by approximately 500mW.

Figure 2. Equivalent Output Circuit

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Analog Output

The device is a differential current-steering DAC with built-in output termination resistors. The outputs are terminated to AV_{DD3.3}, providing a 50 Ω differential output resistance. As mentioned in the <u>Reference System</u> section, a constant-current sink is connected to each DAC output. Figure 2 shows an equivalent circuit of the internal output structure of the device. The circuit has some resistive, capacitive, and inductive elements. These elements limit the output bandwidth to 2GHz with a resistive, differential 50 Ω load.

Figure 3. Typical Output Circuit

The outputs need to be pulled up externally to AV_{DD3.3}. It is recommended that inductors be used for this purpose, as shown in <u>Figure 3</u>. The use of discrete inductors and capacitors allows for near-perfect symmetry in the output circuit layout. Low-resistance wire-wound inductors and high-Q, low-ESR capacitors are recommended. An external 50 Ω differential load is also required to avoid excessive voltage swings at the DAC output pins.

Clock Inputs

The device has a universal, differential clock input (CLKP, CLKN) operating from a separate power supply (AV_{CLK}) to achieve the best possible jitter performance. The two clock inputs should be driven from a differential clock source. A sine-wave or square-wave signal can be used. For the highest speeds and highest performance, a sinusoidal clock should be used. At rates where it is feasible, an LVDS or PECL clock can also be used. The LVDS or PECL clock must be AC-coupled to the device. Each pin is internally DC biased to 1/3 of the supply voltage AV_{CLK}.

The clock input has an internal 100Ω differential termination resistor. For 50Ω (differential) termination, an additional external termination resistor is required between CLKP and CLKN. The balanced input should be AC-coupled unless the common mode of the clock source is within the specifications for the device's clock input. An example of a well-balanced single-ended to differential application circuit using three baluns is shown in Figure 4.

Figure 4. Balanced Clock Interface Circuit

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Data Inputs

The device supports both single data-rate (SDR) and double data-rate (DDR) data interfaces. The data inputs (DxP[13:0] and DxN[13:0] (where x = A, B, C, and D), XORP, XORN, PARP, PARN, SYNCP, and SYNCN) all accept LVDS or differential high-speed transceiver logic (DHSTL) signal levels. DCLKRSTP/DCLKRSTN is also a differential input, but requires a higher signal swing than the LVDS signal pairs and does not support DHSTL levels.

The device can accept data in either 2:1 or 4:1 mux modes. The f_{CLK} input clock is divided internally to create the internal clock used to latch input data. The frequency of this internal clock is determined by the mux mode employed and is either $f_{CLK}/2$ when in 2:1 mode (MUX = 0), or $f_{CLK}/4$ when in 4:1 mode (MUX = 1). An additional user-enabled divide-by-2 (DCLKDIV = 1) is available to reduce the DCLKP/DCLKN output frequency, providing a lower frequency reference clock that can be used to synchronize the data source and the device.

The data sequence in 4:1 mux mode is DA1, DB1, DC1, DD1, DA2, DB2, etc. Only ports B and C are used when operating in 2:1 mux mode. The output is updated in the sequence of DB1, DC1, DB2, DC2, etc. The RFZ frequency response mode uses only ports A and C. The data sequence for the RFZ mode is DA1, DC1, DA2, DC2, etc.

When the device is only used in the 2:1 mux or RFZ modes, the unused data inputs (ports A and D for 2:1 mux mode and ports B and D for RFZ mode) should be connected to GND. Note that the scan function does not work in 2:1 or RFZ modes. Alternatively, any unused ports can be simply driven with LVDS logic-low when not in use. The scan feature is then functional when needed, as well as the ability to easily change the operating mode to meet specific signal-generation requirements.

Table 1 shows the supported data rates, port configurations, and DCLKP/DCLKN frequencies for all operating modes.

Figure 5 shows a simplified block diagram for a clocking scheme using an FPGA and the device DLL. The f_{CLK} input clock to the device is divided by two to produce the f_{CLK}/2 clock that is equal to the input data rate when operating in 2:1 mux mode. The f_{CLK}/2 signal feeds a variable delay line and an optional divide-by-2 block to produce the DCLK signal that is sent to the FPGA. By adjusting the delay of the DCLK signal, the phase of the input data can be adjusted. The device's DLL is used to lock the phase of the incoming data to the internal clock that is used to latch the data. The incoming SYNC signal is used to close the DLL loop and is a replica of the other data lines, but with a pseudorandom data pattern.

The clock-management circuitry (CMC) should not be placed inside the DLL loop and is not needed for clocking the output data and output serializer/deserializer (SerDes) to the DAC. However, it can be used to generate internal clocks, locked to DCLK, for any data FIFO and internal logic. The buffered DCLK without the CMC is used to clock the output SerDes. One output SerDes, with its data wired in such a manner as to reduce its function to that of a simple buffer, is used to match the timing of the SYNC signal to the FPGA output data. This adds between 1ns and 3ns delay on SYNC referenced to the device's DCLK output.

When the device is configured with the optional internal divide-by-2 turned off, the output clock rate must be divided by two (or more) externally for some generations of FPGAs.

мих	DCLKDIV	FREQUENCY- RESPONSE MODE	ACTIVE INPUT PORTS	DCLKP/DCLKN OUTPUT FREQUENCY	MAXIMUM INPUT DATA RATE PER PORT (Msps)
0	0	NRZ, RZ, RF	B, C	f _{CLK} /2	1150
0	1	NRZ, RZ, RF	B, C	f _{CLK} /4	1150 (DDR)
1	0	NRZ, RZ, RF	A, B, C, D	f _{CLK} /4	575
1	0	RFZ	A, C*	f _{CLK} /4	575
1	1	NRZ, RZ, RF	A, B, C, D	f _{CLK} /8	575 (DDR)
1	1	RFZ	A, C*	f _{CLK} /8	575 (DDR)

Table 1. Data Interface Operating Modes

*Ports B and D are internally zero stuffed. Parity is calculated for A and C ports only.

Figure 5. Interfacing the MAX5879 to an FPGA

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DAC Impulse/ Frequency-Response Modes

The device has four user-selectable DAC impulse/ frequency-response modes. The four impulse responses are shown in <u>Figure 6</u>. The modes are set using the RZ and RF input pins, as shown in <u>Table 2</u>.

The default operating mode, and typical of most DACs, is NRZ mode. Using this mode, the frequency response of the DAC has the familiar sync shape, with zeroes at every multiple of the DAC update frequency. The theoretical frequency response for the NRZ mode of operation is shown in <u>Figure 7</u>. The amplitude for a specific output frequency, relative to the maximum output power, can be calculated as follows:

$$A_{NRZ} = A_0 \left| \frac{\sin(\pi f_{OUT} T)}{\pi f_{OUT} T} \right|$$

where T is 1/f_{DAC}.

In RZ mode, the DAC output has a duty cycle determined by the clock input duty cycle. The DAC output is midscale when CLKP/CLKN is a logic-low, and set by the data input when CLKP/CLKN is logic-high. This causes the output amplitude and frequency rolloff of the DAC to be scaled by the duty cycle. The amplitude for a specific output frequency, relative to the maximum output power, can be calculated as follows:

$$A_{RZ} = \frac{A_0}{2} \left| \frac{\sin(\pi f_{OUT} T/2)}{\pi f_{OUT} T/2} \right|$$

where T is 1/f_{DAC}.

Table 2. Frequency-Response Selection

RZ	RF	OPERATING MODE
0	0	NRZ
1	0	RZ
0	1	RF
1	1	RFZ*

*MUX = 1 only; use channels A and C. Channels B and D are internally zero stuffed. Parity is calculated for the A and C ports only.

This frequency response is flatter than the NRZ response in the first three Nyquist zones, and particularly in the 2nd and 3rd Nyquist zones, making the DAC usable for outputting wideband signals in these zones. The trade-off when using this mode is lower maximum power in the 1st Nyquist zone. The theoretical frequency response for the RZ mode of operation is shown in Figure 8.

The third mode of operation is called RF mode. This is similar to mixing the DAC output with the DAC update clock. In this mode, the amplitude response is:

$$A_{RF} = A_0 \left| \frac{\sin(\pi f_{OUT}T/2)}{\pi f_{OUT}T/2} \sin(\pi f_{out}T/2) \right|$$

where T is 1/f_{DAC}.

The theoretical frequency response for the RF mode of operation is shown in Figure 9.

The final mode of operation is called RFZ mode and is a combination of the RF and RZ modes. It is only available in the 4:1 mux input mode. This mode offers a spectral response that is flat over a wider bandwidth than the other modes. Note that f_{DAC} is $f_{CLK}/2$ for the RFZ mode.

$$A_{RFZ} = \frac{A_0}{2} \left| \frac{\sin(\pi f_{OUT} T/4)}{\pi f_{OUT} T/4} \sin(\pi f_{OUT} T/4) \right|$$

where T is 1/f_{DAC}.

The theoretical frequency response for the RFZ mode of operation is shown in Figure 10.

The achievable output power at any one frequency and in any mode is found by normalizing the output power to the low-frequency NRZ response (0dB in Figure 7).

It is clear that the NRZ mode provides the highest power in the 1st Nyquist zone. The RZ mode provides the flattest frequency response in the 1st and 3rd Nyquist zones, and the RF mode provides superior output power in the 2nd and 3rd Nyquist zones, as well as the flattest gain in the 2nd Nyquist zone. The RFZ mode provides the flattest response across the 3rd through 5th Nyquist zones.

Figure 6. Impulse Responses in (a) NRZ Mode, (b) RZ Mode, (c) RF Mode, and (d) RFZ Mode **Note:** T = 1/f_{DAC}

Figure 7. Theoretical Frequency Response (NRZ Mode)

Figure 8. Theoretical Frequency Response (RZ Mode)

Figure 9. Theoretical Frequency Response (RF Mode)

Figure 10. Theoretical Frequency Response (RFZ Mode)

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DLL Frequency Selection and 4-Level Input

Two external pins (DLLOFF and DELAY) have 4-level inputs (high, low, open, and resistor to ground) that perform the following functions:

- Turn DLL on or off
- Select operating frequency range of DLL

Table 3 defines the functionality of the DLLOFF and DELAY controls. Figure 11 shows the block diagram of the 4-level input circuitry.

Note: Reset the DLL circuitry at power-up and each time the frequency range is changed. Set DLLOFF = 1 prior to selecting the range to perform the reset.

Figure 11. 4-Level Input for DLLOFF and DELAY Pins

MUX	DLLOFF	DELAY	fCLK	(MHz)	f _{DLL}	(MHz)	OPERATION
	High	High	_	_	_	_	DLL disabled, one f _{CLK} period delay added to the DCLKP/DCLKN outputs
	High	Low	_	—			DLL disabled, no delay
	Low	High	2150	2300	1075	1150	DLL enabled
	Low	Open	1900	2150	950	1075	DLL enabled
Low	Open	Low	1650	1900	825	950	DLL enabled
	Open	High	1400	1650	700	825	DLL enabled
	Open	Open	1250	1400	625	700	DLL enabled
	Resistor to ground	Low	1100	1250	550	625	DLL enabled
	Resistor to ground	High	950	1100	475	550	DLL enabled
	Resistor to ground	Open	800	950	400	475	DLL enabled
	Resistor to ground	Low	2200	2300	550	575	DLL enabled
High	Resistor to ground	High	1900	2200	475	550	DLL enabled
	Resistor to ground	Open	1600	1900	400	475	DLL enabled

Table 3. Pin Function (DLLOFF, DELAY)

XOR and Parity Inputs

The device includes an XOR data function that can be used to whiten the spectral content of the data bits. Figure 12 shows the XOR and parity calculation. The block labeled "parity calculation" returns a 1 when there is an odd number of 1s in the DAC data. The parity is calculated by the device and compared to the received parity from the FPGA. When the received and calculated parity bits do not match, PERR is set high and held for 48 DCLK cycles to make it easier for the FPGA or supervisory microcontroller to monitor asynchronously. Note that the FPGA also XORs the parity bit before sending it to the device. This ensures that corruption of the XOR bit results in detected parity errors.

The XORP/XORN and PARP/PARN signals include pipeline delays internal to the device. These delays must be compensated for in the data source in order for them to align to the data within the device. XORP/XORN requires one DCLK cycle delay and PARP/PARN requires three.

SO/LOCK Signal

The SO/LOCK pin is a dual-mode output signal. When SE is logic-low (0V) the SO/LOCK signal indicates the lock condition of the DLL circuit; SO/LOCK is logic-high (1.8V) when the DLL is locked.

The second function of the SO/LOCK signal is an output of the data input register on the device. Setting SE to logic 1 configures the input data register flip-flops into a 56-bit shift register connected to the SO/LOCK output, as shown in Figure 13. The contents of the shift register are output on the SO/LOCK pin, allowing verification of connectivity in the data interface.

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Figure 12. XOR and Parity Functions

Note: Parity is calculated for the DA, DC, and XOR inputs only for the RFZ mode. Parity is calculated for the DB, DC, and XOR inputs only for the 2:1 mux mode. Parity is calculated for the DA, DB, DC, DD, and XOR inputs for the 4:1 mux mode (excludes RFZ mode).

Figure 13. Input Register Flip-Flops in (a) Normal Operation and (b) Scan Mode **Note:** Scan function is not supported in 2:1 mux or RFZ modes.

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A timing diagram for the scan operation is shown in Figure 14. Known input data is applied to the DAC data inputs on the first DCLK pulse, and the input register is loaded in a parallel fashion. Note that the input data needs one clock cycle to propagate before SE can be set to logichigh. When SE is set to logic-high, the input shift register is activated and the serial-data stream is output at the SO/LOCK pin at the input data rate (fDATA). The SCAN sequence outputs a total of 238 bits. The first bit, output immediately upon transitioning SE to the high state, is the SYNC bit. The next 179 bits are undefined. The LVDS input bits are next in the sequence starting with QD0 and continuing through QA13. The final two bits are PAR followed by XOR. SE must be transitioned low to return SO/ LOCK to the lock function or to perform another SCAN sequence.

SE and SO/LOCK are a 1.8V CMOS logic interface intended for low-frequency operation. The DAC input clock frequency should be lower than normal when using the scan functionality.

Multiple DAC Synchronization

Multiple analog outputs with accurately known relative phase must be generated in many transmit applications. In a quadrature modulator (Figure 15), the I and Q channels must have a well-defined phase relationship to achieve image rejection. In Figure 15, the delays of DAC1 and DAC2 must be well matched. In transmitters using digital beamforming, accurate control of the relative phase of a large number of D/A converters could be needed.

When using a DAC with multiplexed inputs, such as the MAX5879, or an interpolating DAC with a data clock

Figure 14. Timing Diagram (Scan Operation)

Figure 15. DACs and First Upconversion Stage of I/Q Transmitter Using Mux DACs

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output, the input data rate is 1/N times the DAC update rate, and the DAC is latching data on one or both data clock transitions. In the MAX5879, N = 2 or 4, and the input data rate is 1/2 or 1/4 the DAC update rate. The DAC outputs a data clock (DCLK) that is derived from the input clock with a digital clock divider. When the DAC is powered up, the digital clock divider can start up in any one of N states. If multiple DACs are used, the clock dividers of different DACs can start up in different states, hence the DACs latch data at different times. Unless this is detected and corrected, different DACs can output data one or more clock cycles delayed with respect to each other. Resetting the clock divider in each DAC avoids this condition. To ensure a robust system, it is necessary to detect a phase error condition and correct it.

The device implements a reset circuit that allows for resetting the DCLK outputs of multple DACs. The circuit functions by resetting the internal counter used to generate the DCLK signal. Prior to performing a reset, the DLL (if used) should be enabled and locked (LOCK = 1). Then assert DCLKRST for a minimum of 20 and maximum of 40 DAC clock cycles. DCLKRST is then transitioned low and the DCLK output starts after an additional 17 DAC clock cycles. Note that in DDR mode (DCLKDIV = 1), the DCLK output signal of multiple devices can be 180° out of phase.

Applications Information

Output Coupling

The differential voltage between OUTP and OUTN can be converted to a single-ended voltage using a transformer or a differential-amplifier configuration. The DAC outputs should be pulled up to $AV_{DD3.3}$. It is recommended to use bias tees built from discrete inductors and capacitors for the pullups. Two recommended output-circuit configurations are shown in Figure 16. To achieve the maximum bandwidth, minimize the inductance in the ground lead on the secondary side of the transformer. Use a very short trace and multiple vias for the connection to the ground plane.

Grounding, Bypassing, Power-Supply, and Board-Layout Considerations

Grounding and power-supply decoupling can influence the performance of the device. Unwanted digital crosstalk can couple through the input, reference, power supply, and ground connections, affecting dynamic performance. Proper grounding and power-supply decoupling guidelines for high-speed, high-frequency applications should be closely followed. This reduces EMI and internal crosstalk that can significantly affect the dynamic performance of the device.

Use of a multilayer PCB with separate ground and powersupply planes is required. It is recommended that the analog output and the clock input are run as controlledimpedance microstrip lines on the top layer of the board,

Figure 16. (a) Balun Transformer Output and (b) Amplified Output Configuration

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directly above a ground plane, and that no vias are used for the clock input (CLKP, CLKN) and the analog output (OUTP, OUTN) signals. Depending on the length of the traces, and the operating condition, a low-loss dielectric material (such as ROGERS RO4003) as the top-layer dielectric may be advisable. The data clock (DCLKP, DCLKN) must be routed so its coupling into the clock input and the DAC output is minimized.

Digital input signals should be run as controlled-impedance striplines between ground planes. Digital signals should be kept as far away from sensitive analog inputs, reference input sense lines, common-mode inputs, and clock inputs as practical. It is particularly important to minimize coupling between digital signals and the clock to optimize dynamic performance for high output frequencies. A symmetric design of the clock input and analog output lines is critical to minimize distortion and optimize the DAC's dynamic performance. Digital signal paths should be kept short and run lengths matched to avoid data delay mismatch.

The device supports three separate power-supply inputs for analog 3.3V (AV_{DD3.3}), switching (V_{DD1.8}), and clock (AV_{CLK}) circuits. Each AV_{DD3.3}, V_{DD1.8}, and AV_{CLK} input should at least be decoupled with a separate 47nF capacitor as close as possible to the input and their opposite ends with the shortest possible connection to the corresponding ground plane, to minimize loop inductance. All three power-supply voltages should also be decoupled at the point they enter the PCB with tantalum or electrolytic capacitors. Ferrite beads with additional decoupling capacitors forming a pi-network can also improve performance.

Static Performance Parameter Definitions

Offset Error

The offset error is the difference between the ideal and the actual offset current. For a DAC, the offset point is the average value at the output for the two midscale digital input codes with respect to the full scale of the DAC. This error affects all codes by the same amount.

Gain Error

A gain error is the difference between the ideal and the actual full-scale output voltage on the transfer curve, after nullifying the offset error. This error alters the slope of the transfer function and corresponds to the same percentage error in each step.

Dynamic Performance Parameter Definitions

Settling Time

The settling time is the time between the instant that a step is input to the device and the point where the output reaches the corresponding value and stays within the specified accuracy.

Noise Spectral Density

The DAC output noise is the sum of the quantization noise and other noise sources. Noise spectral density is the noise power in a 1Hz bandwidth.

Spurious-Free Dynamic Range (SFDR)

SFDR is the ratio of the RMS amplitude of the carrier frequency (maximum signal components) to the RMS value of the largest distortion component. SFDR is usually measured in dBc with respect to the carrier frequency amplitude, or in dBFS with respect to the DAC's fullscale range. Depending on its test condition, SFDR is observed within a predefined window or to Nyquist.

Two-/Four-Tone Intermodulation Distortion (IMD)

The two-/four-tone IMD is the ratio expressed in dBc (or dBFS) of the worst 3rd-order (or higher) IMD products to any output tone.

Adjacent Channel Power (ACP)

Adjacent channel power is commonly used in combination with DOCSIS-compliant QAM signals. ACP is the ratio in dB between the power in a channel at a specified frequency offset from the edge of the transmitted channel block, and the power in the lowest frequency channel of the transmitted block. ACP provides a quantifiable method of determining out-of-band spectral energy and its influence on an adjacent channel when a bandwidthlimited RF signal passes through a nonlinear device.

Adjacent Channel Leakage Power Ratio (ACLR)

Commonly used in combination with wideband codedivision multiple access (WCDMA), ACLR reflects the leakage power ratio in dB between the measured powers within a channel relative to its adjacent channel. ACLR provides a quantifiable method of determining out-ofband spectral energy and its influence on an adjacent channel when a bandwidth-limited RF signal passes through a nonlinear device.

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Ordering Information

PART	TEMP RANGE	PIN-PACKAGE
MAX5879EXF+	-40°C to +85°C	256 CSBGA

+Denotes a lead(Pb)-free/RoHS-compliant package.

Package Information

For the latest package outline information and land patterns (footprints), go to <u>www.maximintegrated.com/packages</u>. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

PACKAGE	PACKAGE	OUTLINE	LAND
TYPE	CODE	NO.	PATTERN NO.
256 CSBGA	X25677+10	<u>21-0474</u>	<u>90-0291</u>

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Revision History

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REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	8/11	Initial release	
1	10/12	Updated the <i>Electrical Characteristics</i> , Figures 5, 13, 14 and the <i>SO/LOCK Signal</i> section	6, 47, 54, 55

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